

C1
structures formed on the second layer 48 are chosen to not be able to etch the first layer 44, thereby shielding structures below the second layer 48 from these etching processes.

In the Claims:

Please cancel claim 25.

Please amend claims 14 and 21 to read as follows:

C2
14. (Amended) A method of forming a feature having a critical dimension comprising:

providing a substrate;

forming a first layer having a first thickness;

forming an opening extending through the first layer, the opening having vertical sidewalls separated by a width greater than the critical dimension;

forming a blanket dielectric layer having a second thickness in the opening, on the first layer and on the sidewalls, the second thickness being half or less of the first thickness;

selectively and anisotropically etching the blanket dielectric layer to form dielectric spacers on the sidewalls and to remove the blanket dielectric layer from a bottom of the opening without etching the first layer, the dielectric spacers separated by a gap having a width equal to the critical dimension;

implanting ions into the substrate at a location beneath the dielectric spacers, the implanting being performed at an angle to provide implanted ions under the dielectric spacers on each side of the opening;

forming a second layer in the gap and on the first layer;

removing those portions of the second layer formed on the first layer using a chemical-mechanical polish without removing portions of the second layer in the gaps; and

removing the first layer but not the dielectric spacers.

C3
21. (Amended) A method of forming a feature having a selected dimension comprising:

forming a first layer having a first thickness on a semiconductor substrate;

forming a second layer over said first layer, said second layer having a second thickness thicker than said first layer and being etchable by a different etch chemistry than said first layer;

forming an opening , having vertical sidewalls separated by a width greater than said selected dimensions, said opening extending through said second layer and not through said first layer;

forming a blanket dielectric layer having a third thickness on the second layer and within the opening and on top of the first layer within the opening, said blanket dielectric layer being on the sidewalls of the second layer, the third thickness being half or less that of the second thickness;

selectively and anisotropically etching the blanket dielectric layer to form dielectric spacers on the sidewalls of the second layer and to remove the blanket dielectric layer from a bottom of the opening;

implanting ions into the substrate at a location beneath the opening, the implanting being performed at multiple angles to provide implanted ions under the dielectric spacers on each side of the opening;

etching the first layer to expose the substrates and form a gap having a width equal to the selected dimension between the dielectric spacers;

forming a fourth layer in the gap and on the substrate; and

removing any remaining portions of the second layer without removing the dielectric spacers.

Please add new claim 26 to read as follows:

26. (New) The method according to claim 14 wherein the implants are performed at multiple angles.